

AMENDMENTS TO THE SPECIFICATION:

Please replace the Abstract and with the following amended Abstract:

The present invention relates to a programmable memory device and a method of setting a state for a programmable memory device. In at least one embodiment, the memory device comprises at least a level shifter adapted to ~~standoff~~ stand off a high programming voltage to at least one fuse element in the memory device, wherein the high ~~programmable~~ programming voltage is used to set a state of the memory device.